

isc N-Channel MOSFET Transistor

IRFSL4410Z

• FEATURES

- Static drain-source on-resistance:
 R_{DS}(on) ≤9.0mΩ
- Enhancement mode
- · Fast Switching Speed
- 100% avalanche tested
- Minimum Lot-to-Lot variations for robust device performance and reliable operation

DESCRITION

· reliable device for use in a wide variety of applications

g(1) s(3) pin 1, Gote 2, Drain 3, Source TO-262 package

• ABSOLUTE MAXIMUM RATINGS(Ta=25°C)

| SYMBOL | PARAMETER | VALUE | UNIT |
|------------------|---|---------|--------------|
| V_{DSS} | Drain-Source Voltage | 100 | V |
| V_{GS} | Gate-Source Voltage | ±20 | V |
| I _D | Drain Current-Continuous | 97 | Α |
| I _{DM} | Drain Current-Single Pulsed | 390 | Α |
| P_D | Total Dissipation @T _C =25°C | 230 | W |
| Тј | Max. Operating Junction Temperature | 175 | $^{\circ}$ C |
| T _{stg} | Storage Temperature | -55~175 | $^{\circ}$ |

• THERMAL CHARACTERISTICS

| SYMBOL | PARAMETER | MAX | UNIT |
|-----------|------------------------------------|------|------|
| Rth(ch-c) | Channel-to-case thermal resistance | 0.65 | °C/W |

| 0 1 G | 13 | A2 | | F |
|-------|-----|---------------|-------|---|
| , | | n | ım | |
| | DIM | MIN | MAX | |
| | A | 4.37 | 4.77 | |
| | A1 | 1.22 | 1.42 | |
| | A2 | 2.47 | 2.87 | |
| | Ъ | 0.70 | 0.97 | |
| | Ъ2 | 1.17 | 1.42 | |
| | С | 0.28 | 0.53 | |
| | D | 23.20 | 24.02 |] |
| | D1 | 8.38 | 8.90 | |
| , | D2 | 6.00 | -83 | |
| | E | 9.90 | 10.39 | |
| | E4 | 7.30 | |] |
| | е | 2.54BSC | | |
| , | G | 1.25 | 1.50 | |
| | H2 | 8 | 1.31 | 1 |
| | L | 13.34 | 14.10 | 1 |
| | L1 | 3.30 | 4.06 | |
| | L3 | 0.95 | 1.15 | |



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ELECTRICAL CHARACTERISTICS

T_C=25℃ unless otherwise specified

| SYMBOL | PARAMETER | CONDITIONS | MIN | ТҮР | MAX | UNIT |
|---------------------|--------------------------------|--|-----|-----|------|------|
| BV _{DSS} | Drain-Source Breakdown Voltage | V _{GS} =0V; ID =250 μ A | 100 | | | V |
| V _{GS(th)} | Gate Threshold Voltage | V _{DS} =V _{GS} ; ID =150 μ A | 2.0 | | 4.0 | V |
| R _{DS(on)} | Drain-Source On-Resistance | V _{GS} =10V; I _D =58A | | | 9.0 | mΩ |
| I _{GSS} | Gate-Source Leakage Current | V _{GS} =±20V | | | ±0.1 | μА |
| I _{DSS} | Drain-Source Leakage Current | V _{DS} =100V; V _{GS} = 0V | | | 20 | μА |
| V _{SD} | Diode forward voltage | Is=58A, V _{GS} = 0 V | | | 1.3 | V |

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